

FPA-3030i5a i-line Stepper for Power Device, IoT & 5G Device Applications



High-Resolution i-line Stepper for ≤ 200 mm Wafer Fabrication

FPA-3030i5a Steppers deliver performance and flexibility required for manufacturing and R&D environments, and support a variety of substrates including SiC, GaAs, GaN, sapphire and transparent wafers.

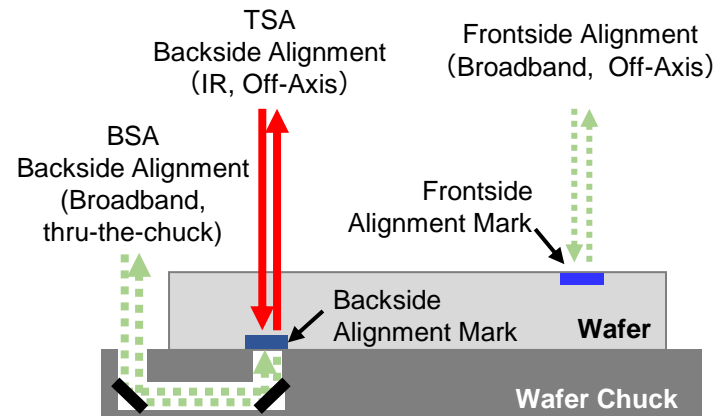
The FPA-3030i5a supports a range of wafer sizes for innovative Internet-of-Things (IoT), 5G, automotive, power and Micro-electromechanical Systems (MEMS) applications and can be configured to process wafers from 50 mm (2") to 200 mm (8") in diameter. FPA-3030i5a systems can also be configured to handle two different wafer sizes with the Multi-Wafer Handling Kit option.

FPA-3030i5a Features

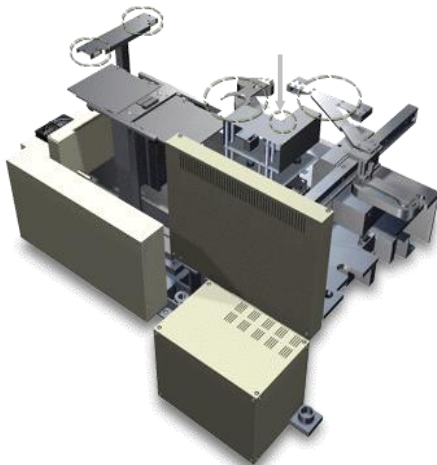
- Resolution ≤ 350 nm
- Reduction 5:1
- Substrate handling capability: 50, 75, 100, 150, 200 mm
- Canon Built-In Metrology (CANOMAP)

Key Options

- Through-Silicon Alignment (TSA-D Scope)
- Through-the-Chuck Alignment (E-Scope)
- Die-by-Die Overlay Compensation (EAGA)
- Multi-Wafer Size Handling Kit
 - 75 & 100 mm, 100 & 150 mm, 150 & 200 mm
- Warped/Bonded/Transparent Wafer Handling
- Pellicle Particle Checker
- PC Remote Console
- GEM-compliant Online Software



FPA-3030 Stepper Backside Alignment Options enable front-to-back overlay alignment



Multi-Wafer Size Kits allow easy wafer size modification
75 \leftrightarrow 100 mm, 100 \leftrightarrow 150 mm, 150 \leftrightarrow 200 mm

FPA-3030i5a Specifications

Technology	i-line Stepper (365 nm)
Resolution	≤ 350 nm
Throughput	≥ 105 wph (200 mm)
Single Machine Overlay	≤ 40 nm (Front) ≤ 150 nm (Back)*
Numerical Aperture	0.45 – 0.63
Exposure Field	22 x 22 mm
Substrate Size Options*	50, 75, 100, 125, 150, 200 mm
Dimensions (W x D x H)	1.9 x 2.6 x 2.45 m

* = Options Required

Canon Lithography System Lineup

Canon Photolithography equipment is designed to help provide exceptional quality, performance, and cost of ownership for your wafer imaging applications.

Canon FPA (Fine Pattern Aligner) Series Nanoimprint, i-line and Deep Ultraviolet (DUV) lithography systems are used in the fabrication and heterogeneous integration of high-tech devices including integrated circuits, hard disk read/write heads, microelectromechanical systems (MEMS) devices, image sensors, displays, power devices and light emitting diodes (LED).

Litho Product	Technology	Resolution	Lens Reduction Field Size [mm]	Substrate Options [mm]
FPA-6300ES6a	KrF (248 nm) Scanner	≤ 100 nm (≤ 90 nm 2/3 Ann)	4:1 26 x 33	200 300
FPA-6300ESW	KrF (248 nm) Scanner	≤ 130 nm	3.125:1 33 x 42.2	200 300
FPA-5550iZ2	i-line (365 nm) Stepper	≤ 350 nm (≤ 280 nm 2/3 Ann)	4:1 26 x 33	200 300
FPA-5520iV LF2	i-line (365 nm) Stepper	≤ 0.8 μm	2:1 52 x 68	300
FPA-5550iX	i-line (365 nm) Stepper	≤ 0.5 μm	2:1 50 x 50	300
FPA-8000iW	i-line (365 nm) Panel Stepper	≤ 0.8 μm	2:1 52 x 68	515 x 515 (panels)
FPA-3030EX6	KrF (248 nm) Stepper	≤ 150 nm	5:1 22 x 22	50, 75, 100, 125, 150, 200
FPA-3030i5a	i-line (365 nm) Stepper	≤ 350 nm	5:1 22 x 22	50, 75, 100, 125, 150, 200
FPA-3030iWa	i-line (365 nm) Stepper	≤ 0.8 μm	2:1 52 x 52	50, 75, 100, 125, 150, 200
FPA-1200NZ2C	Nanoimprint Lithography	≤ 15 nm	1:1 26 x 33	200 300
MS-001	Wafer Overlay Metrology System	----	----	300

All options may not be available on all models. Contact Canon for details

* = Options Required

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